



Docket No.: M4065.0564/P564-A
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
John T. Moore et al.

Application No.: Not Yet Assigned

Filed: March 1, 2004

Art Unit: Not Yet Assigned

For: GRADED $\text{Ge}_x\text{Se}_{100-x}$ CONCENTRATION Examiner: Not Yet Assigned
IN PCRAM

INFORMATION DISCLOSURE STATEMENT (IDS)

MS Patent Application
Commissioner for Patents
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Dear Sir:

Pursuant to 37 CFR 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO/SB/08. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement accompanies the new patent application submitted herewith.

Copies of the references on the PTO/SB/08 are not provided.

Those patent(s) or publication(s) which are marked with a double asterisk (**) next to the Cite No. in the attached form PTO/SB/08 are not supplied because they were previously cited by or submitted to the Office in a prior application

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number 10/230,327, filed August 29, 2002 and relied upon in this application for an earlier filing date under 35 U.S.C. 120.

The Director is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 04-1073, under Order No. M4065.0564/P564-A. A duplicate copy of this paper is enclosed.

Dated: March 1, 2004

Respectfully submitted,

By 

Thomas J. D'Amico

Registration No.: 28,371

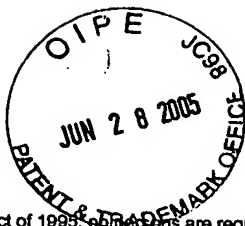
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				First Named Inventor	John T. Moore
				Art Unit	Not Yet Assigned
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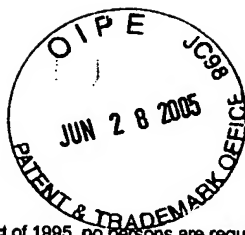
U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
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		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
	BA	WO 02/21542	03/14/2002	Kozicki et al. **		
	BB	WO 00/48196	08/17/2000	Kozicki et al. **		
	BC	WO 97/48032	12/18/1997	Kozicki et al. **		
	BD	WO 99/28914	06/10/1999	Kozicki et al. **		

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¹ Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.



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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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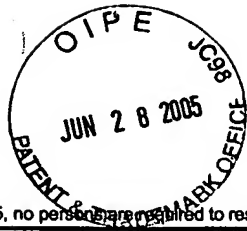
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			Attorney Docket Number	M4065.0564/P564-A
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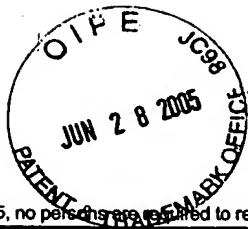
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		Group Art Unit	Not Yet Assigned		
		Examiner Name	Not Yet Assigned		
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